



ZXMN2A01E6

20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	Max R _{DS(ON)}	Max I _D T _A = +25°C (Note 6)
20V	120m Ω @ V _{GS} = 4.5V	3.1A

Description and Applications

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

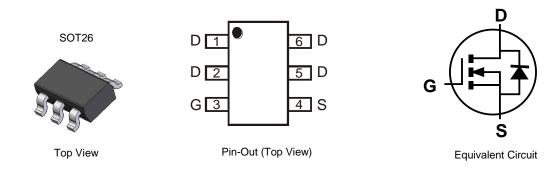
- DC DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

- Low On-resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.016 grams (Approximate)



Ordering Information (Note 4)

Part Number	Marking	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMN2A01E6TA	2A1	7	8	3000
ZXMN2A01E6TC	2A1	13	8	10,000

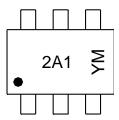
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2A1 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

8

Date	Code	Key

Code

Notes:

Year	2015	2016	2017	2018	2019	2020	2021	2022
Code	С	D	E	F	G	Н	I	J
Month	Jan	Feb Mar	Apr I	Mav Jun	.lul A	ug Sep	Oct N	Nov Dec

6

D

N



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic Drain-Source Voltage		Symbol	Value	Unit	
			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
		$T_{A} = +25^{\circ}C$ (Note 6)		3.1	
Continuous Drain Current	$V_{GS} = 10V$	T _A = +70°C (Note 6)	ID	2.5	А
		$T_{A} = +25^{\circ}C$ (Note 5)		2.5	
Pulsed Drain Current (Note	7)		I _{DM}	11	А
Continuous Source Current (Body Diode) (Note 6)		Is	2.4	А	
Pulsed Source Current (Body Diode) (Note 7)		I _{SM}	11	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^{\circ}C$ (Note 5) Linear derating factor	P _D	1.1 8.8	W mW/°C
Power Dissipation at $T_A = +25^{\circ}C$ (Note 6) Linear Derating Factor	PD	1.7 13.6	W mW/°C
Junction to Ambient (Note 5)	R ₀ JA	113	°C/W
Junction to Ambient (Note 6)	R ₀ JA	70	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	٥C

5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions. Notes:

6. For a device surface mounted on FR-4 PCB measured at t \leq 10 secs.

7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05, pulse width 10µs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

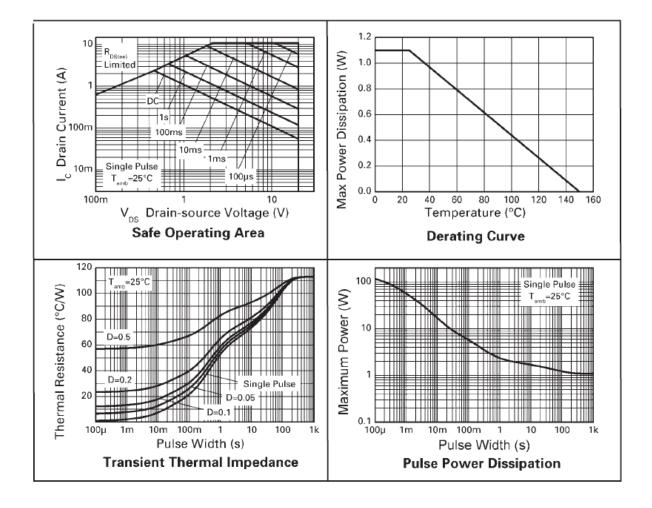
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS						·	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	20	-	-	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	-	-	100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
Gate-Source Threshold Voltage	V _{GS(TH)}	0.7	-	-	V	$I_{D} = 250 \mu A, V_{DS} = V_{GS}$	
Statia Drain Source On State Registeres (Note 8)				0.120	Ω	V _{GS} = 4.5V, I _D =4A	
Static Drain-Source On-State Resistance (Note 8)	R _{DS(ON)}	-	-	0.225	<u> </u>	V _{GS} = 2.5V, I _D =1.5A	
Forward Transconductance (Notes 8 &10)	g fs	-	6.1	-	S	V _{DS} = 10V, I _D =4A	
Diode Forward Voltage (Note 8)	V _{SD}	-	0.9	0.95	V	$T_J = +25^{\circ}C$, $I_S = 3.2A$, $V_{GS} = 0V$	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 10)	Ciss	-	303	-	pF	V _{DS} = 15V, V _{GS} = 0V f = 1MHz	
Output Capacitance (Note 10)	Coss	-	59	-	pF		
Reverse Transfer Capacitance (Note 10)	C _{rss}	-	30	-	pF		
Total Gate Charge (Notes 9 & 10)	Qg	-	3.0	-	nC		
Gate-Source Charge (Notes 9 & 10)	Q _{gs}	-	0.8	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V$	
Gate-Drain Charge (Notes 9 & 10)	Q _{gd}	-	1.0	-	nC	$I_D = 4A$	
Turn-On Delay Time (Notes 9 & 10)	t _{D(ON)}	-	2.49	-	ns		
Turn-On Rise Time (Notes 9 & 10)	t _R	-	5.21	-	ns	$V_{DD} = 10V, V_{GS} = 5V$	
Turn-Off Delay Time (Notes 9 & 10)	t _{D(OFF)}	-	7.47	-	ns	$I_{D} = 4A, R_{G} = 6.0\Omega$	
Turn-Off Fall Time (Notes 9 & 10)	t _F	-	4.62	-	ns	7	
Reverse Recovery Time (Note 10)	t _{RR}	-	23	-	ns	$T_{1} = +25^{\circ}C, I_{F} = 4A,$	
Reverse Recovery Charge (Note 10)	Q _{RR}	-	5.65	-	nC	di/dt= 100A/µs	

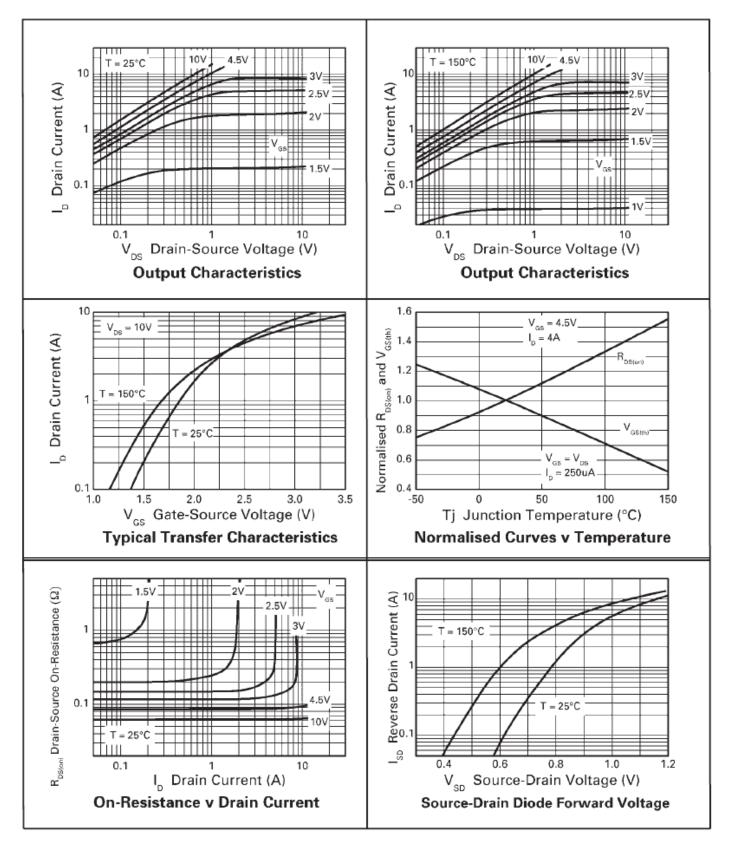
Notes:

8. Measured under pulsed conditions. Width=300µs. Duty cycle ≤ 2%.
9. Switching characteristics are independent of operating junction temperature.
10. For design aid only, not subject to production testing.

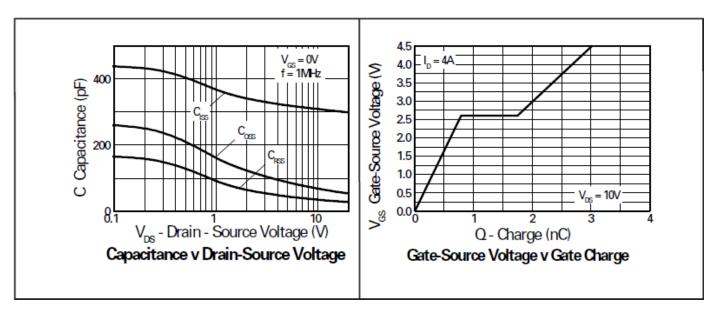


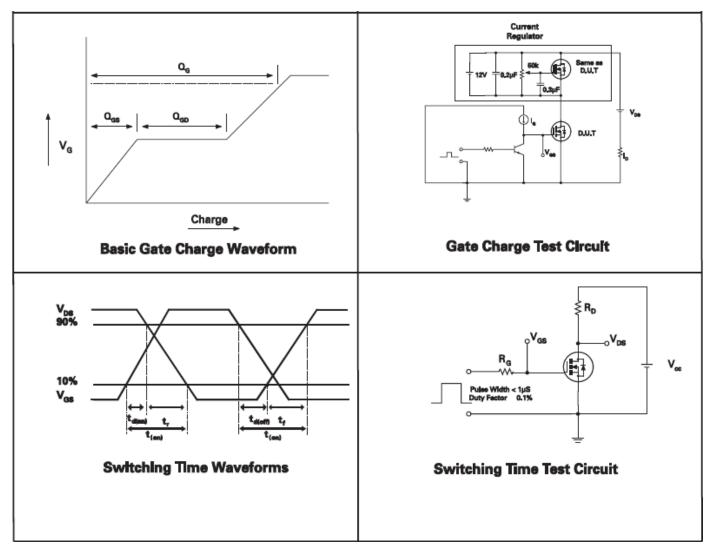








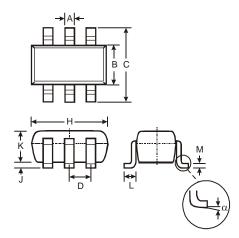






Package Outline Dimensions

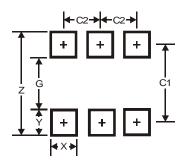
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26					
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D	_		0.95		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
Κ	1.00	1.30	1.10		
L	0.35	0.55	0.40		
М	0.10	0.20	0.15		
α	0°	8°			
All D	imensi	ons in	mm		

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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